Electrically Erasable PROM

FEATURES

- 250 ns Access Time
- Fast Write Cycle Times
  - —64-Byte Page Write Operation
  - —Byte or Page Write Cycle: 5 ms Typical
  - —Complete Memory Rewrite: 2.5 Sec. Typical
  - —Effective Byte Write Cycle Time: 78 μs Typical
- Software Data Protection
- End of Write Detection
  - —$\overline{\text{DATA}}$ Polling
  - —Toggle Bit
- High Reliability
  - —Endurance: 10,000 Writes Per Byte
  - —Data Retention: 100 Years
- Simple Byte and Page Write
  - —Single TTL Level $\overline{\text{WE}}$ Signal
  - —Internally Latched Address and Data
  - —Automatic Write Timing
- Upward Compatible with X2864A
- JEDEC Approved Byte-Wide Pinout

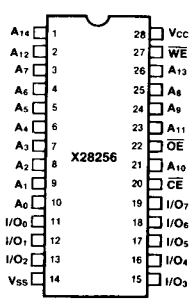
DESCRIPTION

The Xicor X28256 is a 32K x 8 E²PROM, fabricated with Xicor's proprietary, high performance, N-channel floating gate MOS technology. Like all Xicor programmable nonvolatile memories the X28256 is a 5V only device. The X28256 features the JEDEC approved pinout for byte-wide memories, compatible with industry standard RAMs.

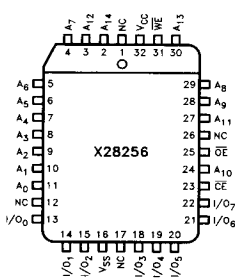
The X28256 supports a 64-byte page write operation, effectively providing a 78 μs/byte write cycle and enabling the entire memory to be typically written in less than 2.5 seconds. The X28256 also features $\overline{\text{DATA}}$ Polling, a system software support scheme used to indicate the early completion of a write cycle. In addition, the X28256 includes a user-optional software data protection mode that further enhances Xicor's hardware write protect capability.

Xicor E²PROMs are designed and tested for applications requiring extended endurance and data retention. Endurance is specified as 10,000 cycles per byte minimum and data retention is specified as 100 years minimum. Refer to Xicor reliability reports RR-520 and RR-515 for details of endurance and data retention characteristics.

PIN CONFIGURATIONS



0029-1

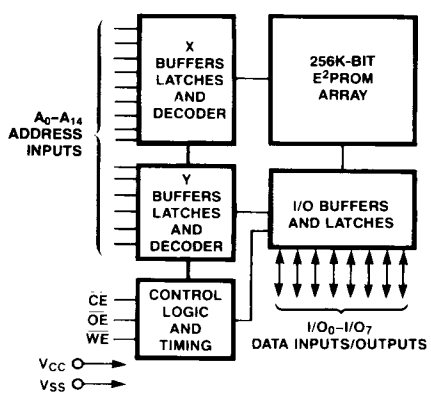


0029-2

PIN NAMES

A_0–A_{14}	Address Inputs
I/O_0–I/O_7	Data Input/Output
$\overline{\text{WE}}$	Write Enable
$\overline{\text{CE}}$	Chip Enable
$\overline{\text{OE}}$	Output Enable
V_{CC}	+5V
V_{SS}	Ground
NC	No Connect

FUNCTIONAL DIAGRAM



0029-3

ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias
X28256 ..... −10°C to +85°C
X28256I ..... −65°C to +135°C
Storage Temperature ..... −65°C to +150°C
Voltage on any Pin with
Respect to Ground ..... −1.0V to +7V
D.C. Output Current ..... 5 mA
Lead Temperature
(Soldering, 10 Seconds) ..... 300°C

*COMMENT

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and the functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. OPERATING CHARACTERISTICS

X28256 T_A = 0°C to +70°C, V_{CC} = +5V ±5%, unless otherwise specified.
X28256I T_A = −40°C to +85°C, V_{CC} = +5V ±5%, unless otherwise specified.

Symbol	Parameter	Limits			Units	Test Conditions
		Min.	Typ.(1)	Max.		
I_{CC}	V_{CC} Current (Active)		60	120	mA	$\overline{CE}$ = $\overline{OE}$ = V_{IL} All I/O's = Open Other Inputs = V_{CC}
I_{SB}	V_{CC} Current (Standby)		35	60	mA	$\overline{CE}$ = V_{IH}, $\overline{OE}$ = V_{IL} All I/O's = Open Other Inputs = V_{CC}
I_{LI}	Input Leakage Current			10	µA	V_{IN} = GND to V_{CC}
I_{LO}	Output Leakage Current			10	µA	V_{OUT} = GND to V_{CC}, $\overline{CE}$ = V_{IH}
V_{IL}(3)	Input Low Voltage	−1.0		0.8	V	
V_{IH}(3)	Input High Voltage	2.0		V_{CC} +0.5	V	
V_{OL}	Output Low Voltage			0.4	V	I_{OL} = 2.1 mA
V_{OH}	Output High Voltage	2.4			V	I_{OH} = −400 µA

TYPICAL POWER-UP TIMING

Symbol	Parameter	Typ.(1)	Units
t_{PUR}(2)	Power-Up to Read Operation	100	µs
t_{PUW}(2)	Power-Up to Write Operation	5	ms

CAPACITANCE T_A = 25°C, f = 1.0 MHz, V_{CC} = 5V

Symbol	Test	Max.	Units	Conditions
$C_{I/O}$(2)	Input/Output Capacitance	10	pF	$V_{I/O}$ = 0V
C_{IN}(2)	Input Capacitance	6	pF	V_{IN} = 0V

A.C. CONDITIONS OF TEST

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	10 ns
Input and Output Timing Levels	1.5V
Output Load	1 TTL Gate and C_L = 100 pF

MODE SELECTION

$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	Mode	I/O	Power
L	L	H	Read	D_{OUT}	Active
L	H	L	Write	D_{IN}	Active
H	X	X	Standby and Write Inhibit	High Z	Standby
X	L	X	Write Inhibit	—	—
X	X	H	Write Inhibit	—	—

Notes: (1) Typical values are for T_A = 25°C and nominal supply voltage.
(2) This parameter is periodically sampled and not 100% tested.
(3) V_{IL} min. and V_{IH} max. are for reference only and are not tested.

ENDURANCE AND DATA RETENTION

Parameter	Min.	Max.	Units	Conditions
Endurance	10,000		Cycles/Byte	Xicor Reliability Report RR-520
Data Retention	100		Years	Xicor Reliability Report RR-515

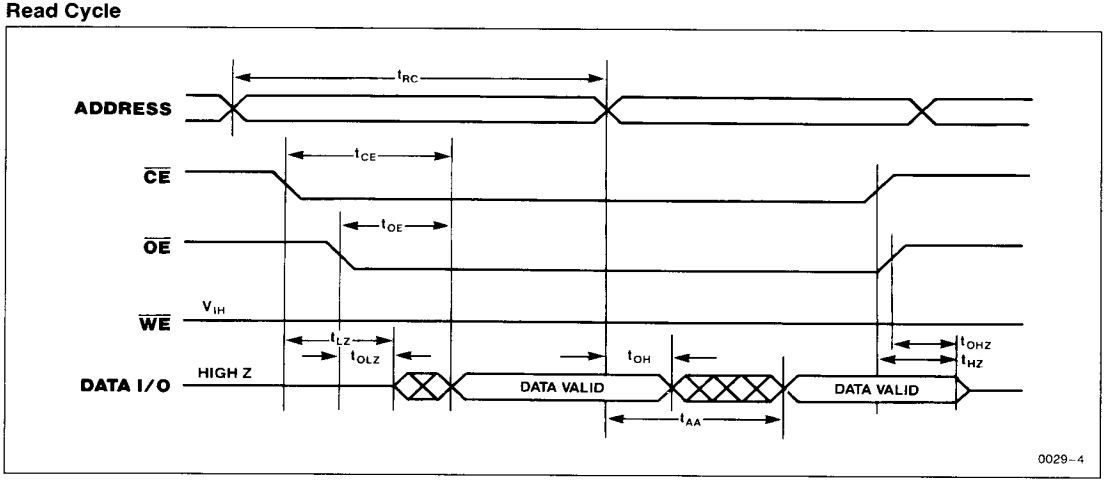
A.C. CHARACTERISTICS

X28256 T_A = 0°C to +70°C, V_{CC} = +5V ±5%, unless otherwise specified.
X28256I T_A = −40°C to +85°C, V_{CC} = +5V ±5%, unless otherwise specified.

Read Cycle Limits

Symbol	Parameter	X28256-25 X28256I-25		X28256 X28256I		X28256-35 X28256I-35		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
t_{RC}	Read Cycle Time	250		300		350		ns
t_{CE}	Chip Enable Access Time		250		300		350	ns
t_{AA}	Address Access Time		250		300		350	ns
t_{OE}	Output Enable Access Time		100		100		100	ns
t_{LZ}(4)	$\overline{CE}$ Low to Active Output	0		0		0		ns
t_{OLZ}(4)	$\overline{OE}$ Low to Active Output	0		0		0		ns
t_{HZ}(4)	$\overline{CE}$ High to High Z Output	0	80	0	80	0	80	ns
t_{OHZ}(4)	$\overline{OE}$ High to High Z Output	0	80	0	80	0	80	ns
t_{OH}	Output Hold from Address Change	0		0		0		ns

Read Cycle

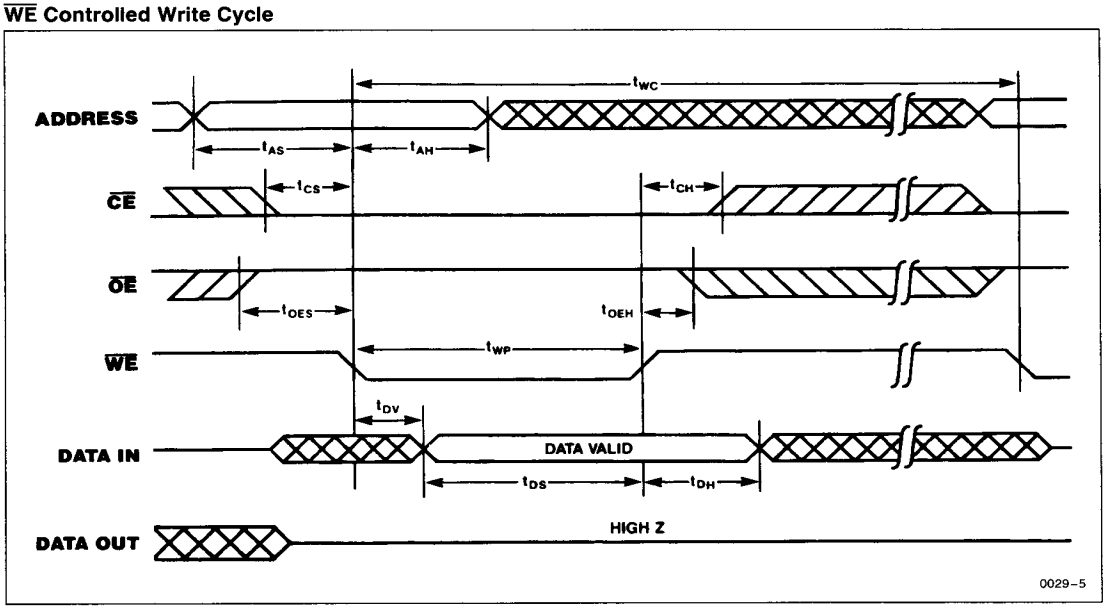


Note: (4) t_{HZ} max. and t_{OHZ} max. are measured from the point when $\overline{CE}$ or $\overline{OE}$ return high (whichever occurs first) to the time when the outputs are no longer driven. t_{HZ} min., t_{OHZ} min., t_{LZ} min. and t_{OLZ} min. are periodically sampled and are not 100% tested.

Write Cycle Limits

Symbol	Parameter	Min.	Typ.(5)	Max.	Units
t_{WC}(6)	Write Cycle Time		5	10	ms
t_{AS}	Address Setup Time	0			ns
t_{AH}	Address Hold Time	150			ns
t_{CS}	Write Setup Time	0			ns
t_{CH}	Write Hold Time	0			ns
t_{CW}	$\overline{CE}$ Pulse Width	150			ns
t_{OES}	$\overline{OE}$ High Setup Time	10			ns
t_{OEH}	$\overline{OE}$ High Hold Time	10			ns
t_{WP}	$\overline{WE}$ Pulse Width	150			ns
t_{WPH}	$\overline{WE}$ High Recovery	1			µs
t_{DV}	Data Valid			300	ns
t_{DS}	Data Setup	100			ns
t_{DH}	Data Hold	15			ns
t_{DW}	Delay to Next Write	10			µs
t_{BLC}	Byte Load Cycle	2		100	µs

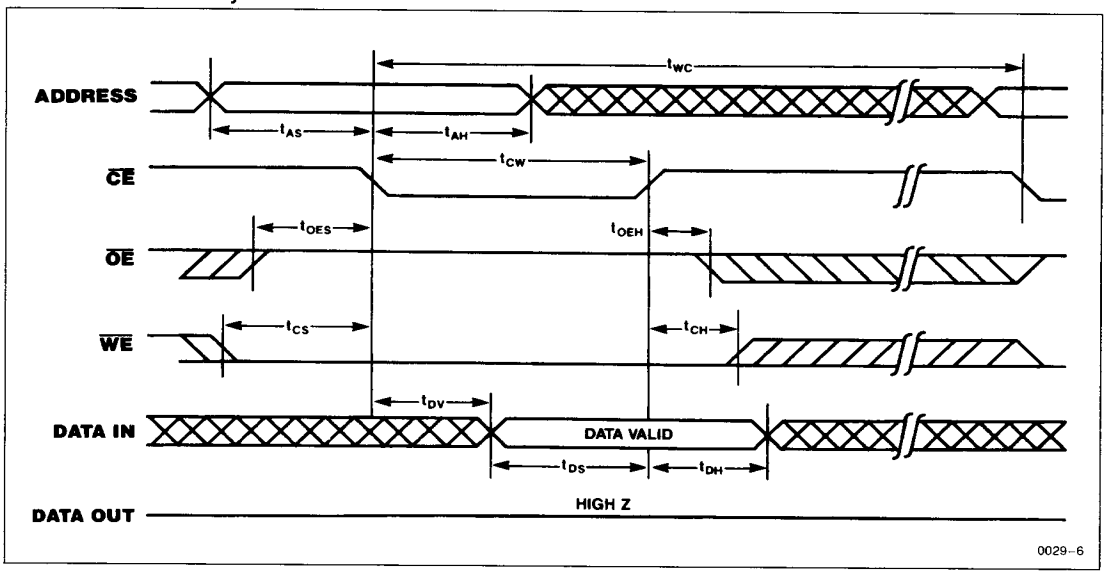
$\overline{WE}$ Controlled Write Cycle



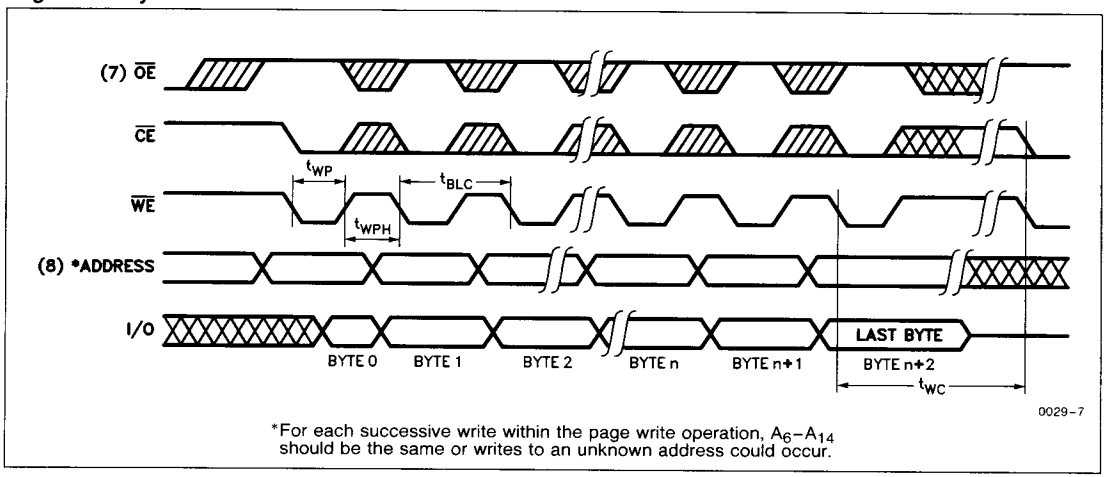
Notes: (5) Typical values are for T_A = 25°C and nominal supply voltage.

(6) t_{WC} is the minimum cycle time to be allowed from the system perspective unless polling techniques are used. It is the maximum time the device requires to automatically complete the internal write operation.

$\overline{CE}$ Controlled Write Cycle



Page Write Cycle

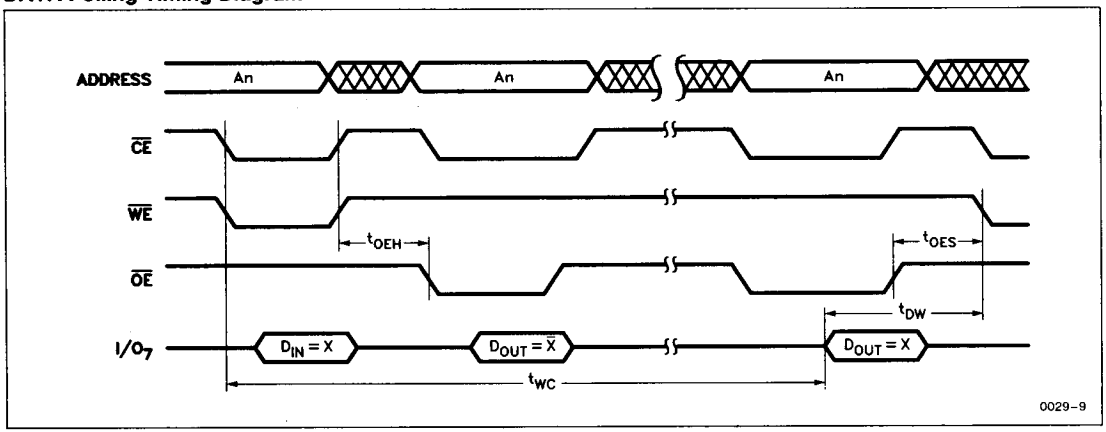


*For each successive write within the page write operation, A_6–A_{14} should be the same or writes to an unknown address could occur.

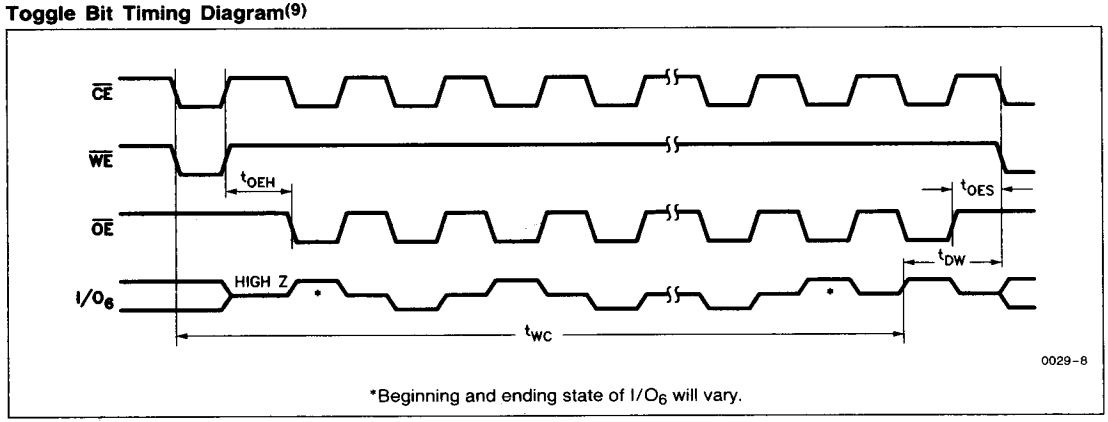
Notes: (7) Between successive byte writes within a page write operation, $\overline{OE}$ can be strobed LOW: e.g. this can be done with $\overline{CE}$ and $\overline{WE}$ HIGH to fetch data from another memory device within the system for the next write; or with $\overline{WE}$ HIGH and $\overline{CE}$ LOW effectively performing a polling operation.

(8) The timings shown above are unique to page write operations. Individual byte load operations within the page write must conform to either the $\overline{CE}$ or $\overline{WE}$ controlled write cycle timing.

$\overline{\text{DATA}}$ Polling Timing Diagram(9)



Toggle Bit Timing Diagram(9)



Note: (9) Polling operations by definition are read cycles and therefore are subject to read cycle timings.

PIN DESCRIPTIONS

Addresses (A_0–A_{14})
The Address inputs select an 8-bit memory location during a read or write operation.

Chip Enable ($\overline{CE}$)
The Chip Enable input must be LOW to enable all read/write operations. When $\overline{CE}$ is HIGH, power consumption is reduced.

Output Enable ($\overline{OE}$)
The Output Enable input controls the data output buffers and is used to initiate read operations.

Data In/Data Out (I/O_0–I/O_7)
Data is written to or read from the X28256 through the I/O pins.

Write Enable ($\overline{WE}$)
The Write Enable input controls the writing of data to the X28256.

DEVICE OPERATION

Read
Read operations are initiated by both $\overline{OE}$ and $\overline{CE}$ LOW. The read operation is terminated by either $\overline{CE}$ or $\overline{OE}$ returning HIGH. This 2-line control architecture eliminates bus contention in a system environment. The data bus will be in a high impedance state when either $\overline{OE}$ or $\overline{CE}$ is HIGH.

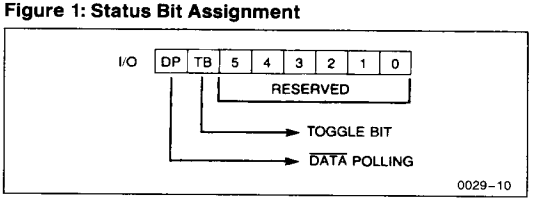
Write
Write operations are initiated when both $\overline{CE}$ and $\overline{WE}$ are LOW *and* $\overline{OE}$ is HIGH. The X28256 supports both a $\overline{CE}$ and $\overline{WE}$ controlled write cycle. That is, the address is latched by the falling edge of either $\overline{CE}$ or $\overline{WE}$, whichever occurs last. Similarly, the data is latched internally by the rising edge of either $\overline{CE}$ or $\overline{WE}$, whichever occurs first. A byte write operation, once initiated, will automatically continue to completion, typically within 5 ms.

Page Write Operation
The page write feature of the X28256 allows the entire memory to be written in 2.5 seconds. Page write allows two to sixty-four bytes of data to be consecutively written to the X28256 prior to the commencement of the internal programming cycle. The host can fetch data from another location within the system during a page write operation (change the source address), but the page address (A_6 through A_{14}) for each subsequent valid write cycle to the part during this operation must be the same as the initial page address.

The page write mode can be initiated during any write operation. Following the initial byte write cycle, the host can write an additional one to sixty-three bytes in the same manner as the first byte was written. Each successive byte load cycle, started by the $\overline{WE}$ HIGH to LOW transition, must begin within 100 μs of the falling edge of the preceding $\overline{WE}$. If a subsequent $\overline{WE}$ HIGH to LOW transition is not detected within 100 μs, the internal automatic programming cycle will commence. There is no page write window limitation. Effectively the page write window is infinitely wide, so long as the host continues to access the device within the byte load cycle time of 100 μs.

Write Operation Status Bits
The X28256 provides the user two write operation status bits. These can be used to optimize a system write cycle time. The status bits are mapped onto the I/O bus as shown in Figure 1.

Figure 1: Status Bit Assignment



$\overline{DATA}$ Polling (I/O_7)
The X28256 features $\overline{DATA}$ Polling as a method to indicate to the host system that the byte write or page write cycle has completed. $\overline{DATA}$ Polling allows a simple bit test operation to determine the status of the X28256, eliminating additional interrupt inputs or external hardware. During the internal programming cycle, any attempt to read the last byte written will produce the complement of that data on I/O_7 (i.e., write data = 0xxx xxxx, read data = 1xxx xxxx). Once the programming cycle is complete, I/O_7 will reflect true data. Note: If the X28256 is in the protected state and an illegal write operation is attempted $\overline{DATA}$ Polling will not operate.

Toggle Bit (I/O_6)
The X28256 also provides another method for determining when the internal write cycle is complete. During the internal programming cycle I/O_6 will toggle from one to zero and zero to one on subsequent attempts to read the device. When the internal cycle is complete the toggling will cease and the device will be accessible for additional read or write operations.

$\overline{DATA}$ POLLING I/O_7

Figure 2a: $\overline{DATA}$ Polling Bus Sequence

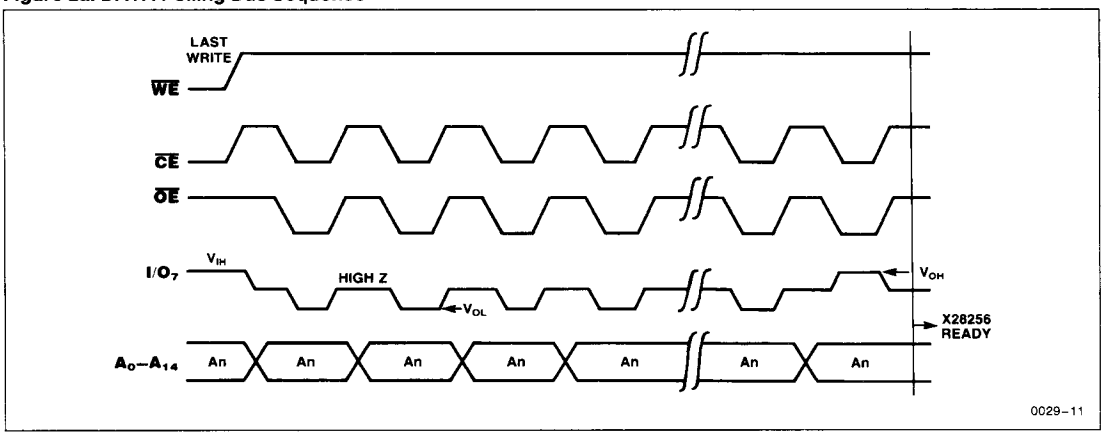
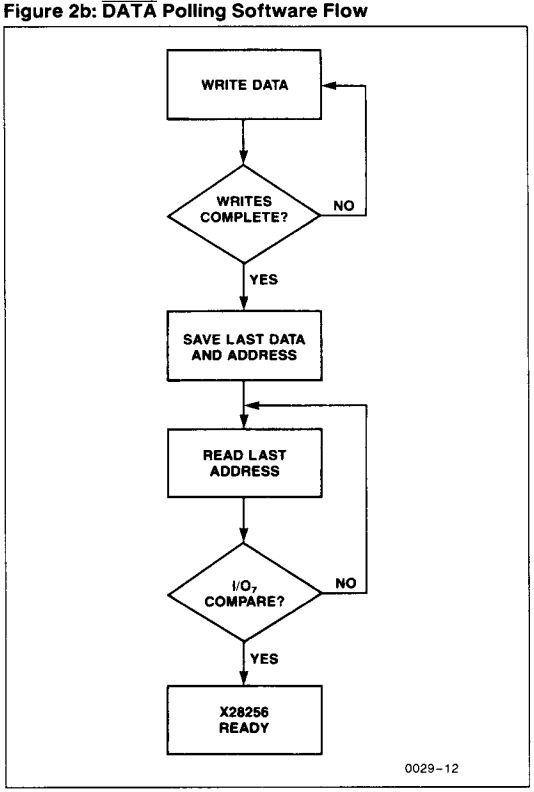


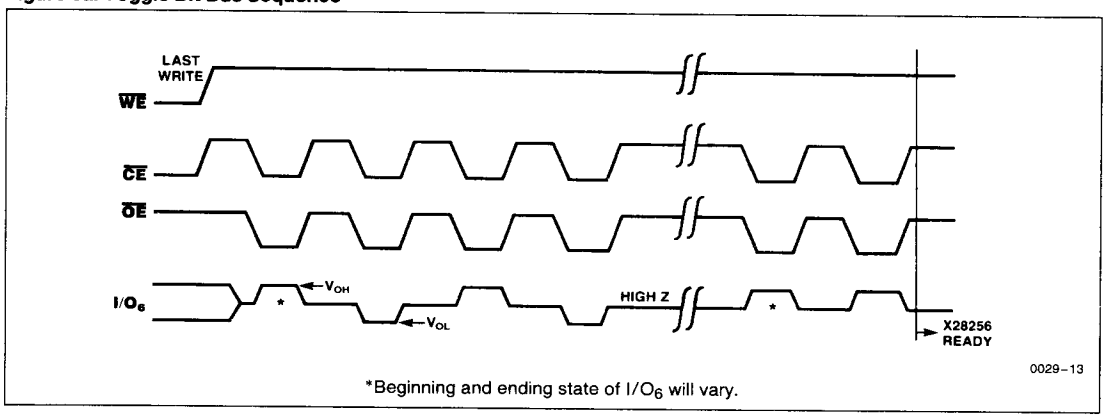
Figure 2b: $\overline{DATA}$ Polling Software Flow



$\overline{DATA}$ Polling can effectively halve the time for writing to the X28256. The timing diagram in Figure 2a illustrates the sequence of events on the bus. The software flow diagram in Figure 2b illustrates one method of implementing the routine.

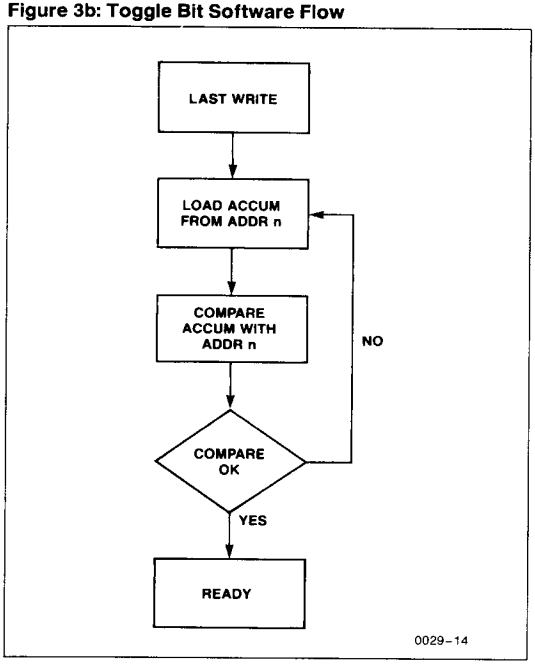
THE TOGGLE BIT I/O_6

Figure 3a: Toggle Bit Bus Sequence



*Beginning and ending state of I/O_6 will vary.

Figure 3b: Toggle Bit Software Flow



The Toggle Bit can eliminate the software housekeeping chore of saving and fetching the last address and data written to a device in order to implement $\overline{DATA}$ Polling. This can be especially helpful in an array comprised of multiple X28256 memories that is frequently updated. Toggle Bit testing can also provide a method for status checking in multiprocessor applications. The timing diagram in Figure 3a illustrates the sequence of events on the bus. The software flow diagram in Figure 3b illustrates a method for testing the Toggle Bit.

HARDWARE DATA PROTECTION

The X28256 provides three hardware features (compatible with X2864A) that protect nonvolatile data from inadvertent writes.

- Noise Protection—A $\overline{WE}$ pulse typically less than 20 ns will not initiate a write cycle.
- Default V_{CC} Sense—All functions are inhibited when V_{CC} is $\leq$3V, typically.
- Write Inhibit—Holding either $\overline{OE}$ LOW, $\overline{WE}$ HIGH, or $\overline{CE}$ HIGH will prevent an inadvertent write cycle during power-on and power-off, maintaining data integrity.

SOFTWARE DATA PROTECTION

The X28256 offers a software controlled data protection feature. The X28256 is shipped from Xicor with the software data protection NOT ENABLED; that is, the device will be in the standard operating mode. In this mode data should be protected during power-up/-down operations through the use of external circuits. The host would then have open read and write access of the device once V_{CC} was stable.

The X28256 can be automatically protected during power-up and power-down without the need for external circuits by employing the software data protection feature. The internal software data protection circuit is enabled after the first write operation utilizing the software algorithm. This circuit is nonvolatile and will remain set for the life of the device unless the reset command is issued.

Once the software protection is enabled, the X28256 is also protected from inadvertent and accidental writes in the powered-on state. That is, the software algorithm must be issued prior to writing additional data to the device.

SOFTWARE ALGORITHM

Selecting the software data protection mode requires the host system to precede data write operations by a series of three write operations to three specific addresses. Refer to Figure 4a and 4b for the sequence. The three byte sequence opens the page write window enabling the host to write from one to sixty-four bytes of data.(10) Once the page load cycle has been completed, the device will automatically be returned to the data protected state.

Note: (10) Once the three byte sequence is issued it must be followed by a valid byte or page write operation.

SOFTWARE DATA PROTECTION

Figure 4a: Timing Sequence—Byte or Page Write

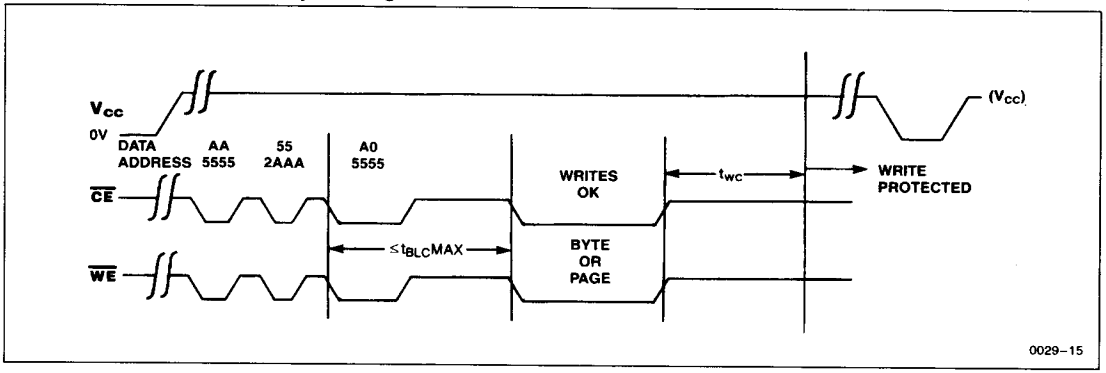
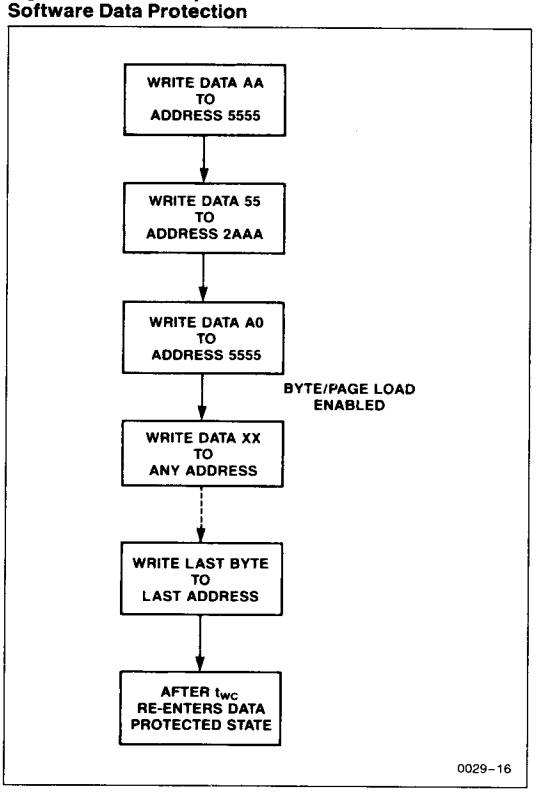


Figure 4b: Write Sequence for Software Data Protection



Regardless of whether the device has previously been protected or not, once the software data protected algorithm is used and data has been written, the X28256 will automatically disable further writes unless another command is issued to cancel it. If no further commands are issued the X28256 will be write protected during power-down and after any subsequent power-up.

Note: Once initiated, the sequence of write operations should not be interrupted.

RESETTING SOFTWARE DATA PROTECTION

Figure 5a: Reset Software Data Protection Timing Sequence

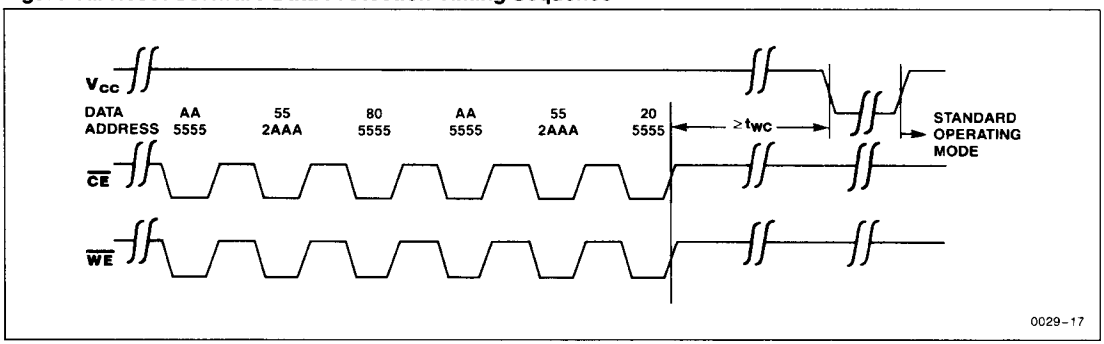
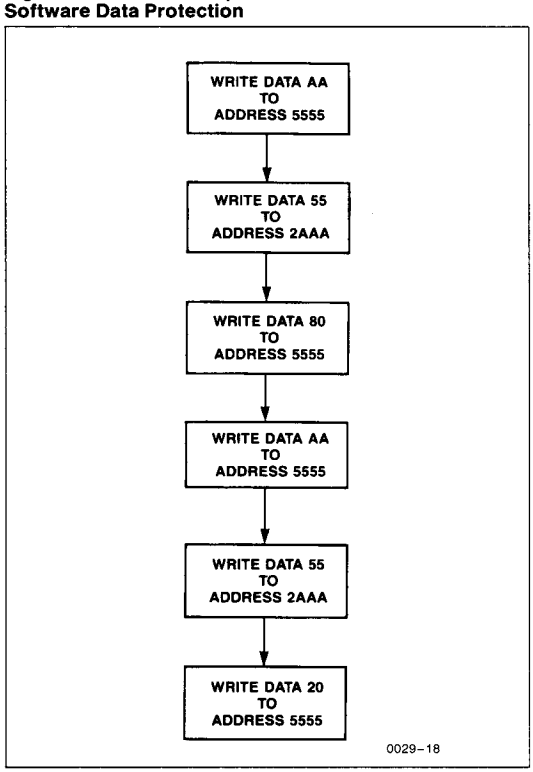


Figure 5b: Software Sequence to Deactivate Software Data Protection



In the event the user wants to deactivate the software data protection feature for testing or reprogramming in an E^2PROM programmer, the following six step algorithm will reset the internal protection circuit. The next time the X28256 is powered-up the device will be in the standard operating mode.

Note: Once initiated, the sequence of write operations should not be interrupted.

SYSTEM CONSIDERATIONS

Because the X28256 is frequently used in large memory arrays it is provided with a two line control architecture for both read and write operations. Proper usage can provide the lowest possible power dissipation and eliminate the possibility of contention where multiple I/O pins share the same bus.

To gain the most benefit it is recommended that $\overline{CE}$ be decoded from the address bus and be used as the primary device selection input. Both $\overline{OE}$ and $\overline{WE}$ would then be common among all devices in the array. For a read operation this assures that all deselected devices are in their standby mode and that only the selected device(s) is outputting data on the bus.

Because the X28256 has two power modes, standby and active, proper decoupling of the memory array is of prime concern. Enabling $\overline{CE}$ will cause transient current spikes. The magnitude of these spikes is dependent on the output capacitive loading of the I/Os. Therefore, the larger the array sharing a common bus, the larger the transient spikes. The voltage peaks associated with the current transients can be suppressed by the proper selection and placement of decoupling capacitors. As a minimum, it is recommended that a 0.1 μF high frequency ceramic capacitor be used between V_{CC} and GND at each device. Depending on the size of the array, the value of the capacitor may have to be larger.

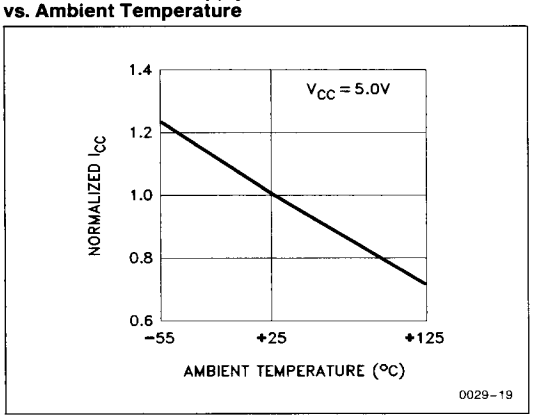
In addition, it is recommended that a 4.7 μF electrolytic bulk capacitor be placed between V_{CC} and GND for each eight devices employed in the array. This bulk capacitor is employed to overcome the voltage droop caused by the inductive effects of the PC board traces.

3

SYMBOL TABLE

WAVEFORM	INPUTS	OUTPUTS
	Must be steady	Will be steady
	May change from Low to High	Will change from Low to High
	May change from High to Low	Will change from High to Low
	Don't Care: Changes Allowed	Changing: State Not Known
	N/A	Center Line is High Impedance

Normalized Active Supply Current vs. Ambient Temperature



Normalized Standby Supply Current vs. Ambient Temperature